Magnus Borgstrm

List of Publications by Year in Descending Order

178 papers	7,968 citations	43 h-index	85 g-index
197 ext. papers	8,630 ext. citations	7.2 avg, IF	5.77 L-index

#	Paper	IF	Citations
178	Realization of axially defined GaInP/InP/InAsP triple-junction photovoltaic nanowires for high performance solar cells. *Materials Today Energy*, **2022**, 101050	7	3
177	Semiconductor nanowire array for transparent photovoltaic applications. *Applied Physics Letters*, **2021**, 118, 191107	3.4	3
176	Comparison of Triethylgallium and Trimethylgallium Precursors for GaInP Nanowire Growth. *Physica Status Solidi (B): Basic Research*, **2021**, 258, 2000400	1.3	1
175	Gain and bandwidth of InP nanowire array photodetectors with embedded photogated InAsP quantum discs. *Nanoscale*, **2021**, 13, 6227-6233	7.7	2
174	Imaging the influence of oxides on the electrostatic potential of photovoltaic InP nanowires. *Nano Research*, **2021**, 14, 4087	10	1
173	Wafer-Scale Synthesis and Optical Characterization of InP Nanowire Arrays for Solar Cells. *Nano Letters*, **2021**, 21, 7347-7353	11.5	2
172	Direct Three-Dimensional Imaging of an X-ray Nanofocus Using a Single 60 nm Diameter Nanowire Device. *Nano Letters*, **2020**, 20, 8326-8331	11.5	6
171	Hot-carrier separation in heterostructure nanowires observed by electron-beam induced current. *Nanotechnology*, **2020**, 31, 394004	3.4	4
170	High resolution strain mapping of a single axially heterostructured nanowire using scanning X-ray diffraction. *Nano Research*, **2020**, 13, 2460-2468	10	5
169	Unravelling processing issues of nanowire-based solar cell arrays by use of electron beam induced current measurements. *Nano Energy*, **2020**, 71, 104575	17.1	8
168	Embedded sacrificial AlAs segments in GaAs nanowires for substrate reuse. *Nanotechnology*, **2020**, 31, 204002	3.4	5
167	Nanowire Solar Cells: A New Radiation Hard PV Technology for Space Applications. *IEEE Journal of Photovoltaics*, **2020**, 10, 502-507	3.7	10
166	Development and Characterization of a bottom-up InP Nanowire Solar Cell with 16.7% Efficiency **2020**,		3
165	Template-assisted vapour-liquid-solid growth of InP nanowires on (001) InP and Si substrates. *Nanoscale*, **2020**, 12, 888-894	7.7	5
164	Operando Surface Characterization of InP Nanowire p-n Junctions. *Nano Letters*, **2020**, 20, 887-895	11.5	8
163	Implementing an Insect Brain Computational Circuit Using III-V Nanowire Components in a Single Shared Waveguide Optical Network. *ACS Photonics*, **2020**, 7, 2787-2798	6.3	0
162	Ultrafast Optical Generation of Coherent Bright and Dark Surface Phonon Polaritons in Nanowires. *ACS Photonics*, **2020**, 7, 1923-1931	6.3	

161	Light current-voltage measurements of single, as-grown, nanowire solar cells standing vertically on a substrate. *Nano Energy*, **2020**, 78, 105191	17.1	8
160	Photovoltaic nanowires affect human lung cell proliferation under illumination conditions. *Nanoscale*, **2020**, 12, 14237-14244	7.7	2
159	Self-Limiting Polymer Exposure for Vertical Processing of Semiconductor Nanowire-Based Flexible Electronics. *ACS Applied Nano Materials*, **2020**, 3, 7743-7749	5.6	7
158	Three-Dimensional Imaging of Beam-Induced Biasing of InP/GaInP Tunnel Diodes. *Nano Letters*, **2019**, 19, 3490-3497	11.5	3
157	Measurements of Strain and Bandgap of Coherently Epitaxially Grown Wurtzite InAsP-InP Core-Shell Nanowires. *Nano Letters*, **2019**, 19, 2674-2681	11.5	11
156	Simultaneous Growth of Pure Wurtzite and Zinc Blende Nanowires. *Nano Letters*, **2019**, 19, 2723-2730	11.5	11
155	Culturing and patch clamping of Jurkat T cells and neurons on AlO coated nanowire arrays of altered morphology.. *RSC Advances*, **2019**, 9, 11194-11201	3.7	7
154	Coulomb blockade from the shell of an InP-InAs core-shell nanowire with a triangular cross section. *Applied Physics Letters*, **2019**, 114, 053108	3.4	7
153	Effect of hydrogen chloride etching on carrier recombination processes of indium phosphide nanowires. *Nanoscale*, **2019**, 11, 18550-18558	7.7	10
152	Revealing misfit dislocations in InAs P -InP core-shell nanowires by x-ray diffraction. *Nanotechnology*, **2019**, 30, 505703	3.4	7
151	Combining Nanofocused X-Rays with Electrical Measurements at the NanoMAX Beamline. *Crystals*, **2019**, 9, 432	2.3	8
150	Radiation Tolerant Nanowire Array Solar Cells. *ACS Nano*, **2019**, 13, 12860-12869	16.7	17
149	Nanoscale mapping of carrier collection in single nanowire solar cells using X-ray beam induced current. *Journal of Synchrotron Radiation*, **2019**, 26, 102-108	2.4	9
148	UV exposure: a novel processing method to fabricate nanowire solar cells **2019**,		1
147	High Responsivity of InP/InAsP Nanowire Array Broadband Photodetectors Enhanced by Optical Gating. *Nano Letters*, **2019**, 19, 8424-8430	11.5	9
146	Nanowire photodetectors with embedded quantum heterostructures for infrared detection. *Infrared Physics and Technology*, **2019**, 96, 209-212	2.7	5
145	Towards Nanowire Tandem Junction Solar Cells on Silicon. *IEEE Journal of Photovoltaics*, **2018**, 8, 733-740	3.7	37
144	Intersubband Quantum Disc-in-Nanowire Photodetectors with Normal-Incidence Response in the Long-Wavelength Infrared. *Nano Letters*, **2018**, 18, 365-372	11.5	27

143	Self-assembled InN quantum dots on side facets of GaN nanowires. *Journal of Applied Physics*, **2018**, 123, 164302	2.5	9
142	Understanding InP Nanowire Array Solar Cell Performance by Nanoprobe-Enabled Single Nanowire Measurements. *Nano Letters*, **2018**, 18, 3038-3046	11.5	52
141	Electrical and optical evaluation of n-type doping in In GaP nanowires. *Nanotechnology*, **2018**, 29, 255701	3.4	4
140	Growth kinetics of Ga InP nanowires using triethylgallium as Ga precursor. *Nanotechnology*, **2018**, 29, 394001	3.4	8
139	InP/GaInP nanowire tunnel diodes. *Nano Research*, **2018**, 11, 2523-2531	10	22
138	Nanobeam X-ray Fluorescence Dopant Mapping Reveals Dynamics of in Situ Zn-Doping in Nanowires. *Nano Letters*, **2018**, 18, 6461-6468	11.5	14
137	Spectrally resolved x-ray beam induced current in a single InGaP nanowire. *Nanotechnology*, **2018**, 29, 454001	3.4	7
136	Bias-dependent spectral tuning in InP nanowire-based photodetectors. *Nanotechnology*, **2017**, 28, 114006	3.4	9
135	Ground State Depletion Nanoscopy Resolves Semiconductor Nanowire Barcode Segments at Room Temperature. *Nano Letters*, **2017**, 17, 2652-2659	11.5	17
134	Absorption and transmission of light in III-V nanowire arrays for tandem solar cell applications. *Nanotechnology*, **2017**, 28, 205203	3.4	23
133	Growth and optical properties of In x Ga1 P nanowires synthesized by selective-area epitaxy. *Nano Research*, **2017**, 10, 672-682	10	24
132	Towards high efficiency nanowire solar cells. *Nano Today*, **2017**, 12, 31-45	17.9	112
131	Room-temperature InP/InAsP Quantum Discs-in-Nanowire Infrared Photodetectors. *Nano Letters*, **2017**, 17, 3356-3362	11.5	28
130	Optimization of Current Injection in AlGaInP Core-Shell Nanowire Light-Emitting Diodes. *Nano Letters*, **2017**, 17, 3599-3606	11.5	13
129	Bending and Twisting Lattice Tilt in Strained Core-Shell Nanowires Revealed by Nanofocused X-ray Diffraction. *Nano Letters*, **2017**, 17, 4143-4150	11.5	34
128	Radial tunnel diodes based on InP/InGaAs core-shell nanowires. *Applied Physics Letters*, **2017**, 110, 113501	3.4	6
127	InGaP Nanowire Growth Dynamics Strongly Affected by Doping Using Diethylzinc. *Nano Letters*, **2017**, 17, 702-707	11.5	25
126	Growth of wurtzite Al Ga P nanowire shells and characterization by Raman spectroscopy. *Nanotechnology*, **2017**, 28, 035706	3.4	5

125	Defect-induced infrared electroluminescence from radial GaInP/AlGaInP quantum well nanowire array light- emitting diodes. *Nanotechnology*, **2017**, 28, 485205	3.4	5
124	InP/InAsP Nanowire-Based Spatially Separate Absorption and Multiplication Avalanche Photodetectors. *ACS Photonics*, **2017**, 4, 2693-2698	6.3	18
123	Cellular traction forces: a useful parameter in cancer research. *Nanoscale*, **2017**, 9, 19039-19044	7.7	34
122	Anti-Stokes photoluminescence probing k-conservation and thermalization of minority carriers in degenerately doped semiconductors. *Nature Communications*, **2017**, 8, 1634	17.4	4
121	Time-resolved photoluminescence characterization of GaAs nanowire arrays on native substrate. *Nanotechnology*, **2017**, 28, 505706	3.4	3
120	Carrier Recombination Processes in Gallium Indium Phosphide Nanowires. *Nano Letters*, **2017**, 17, 4248-4254	12.3	14
119	Growth and optimization of GaInP/InP nanowire tunnel diode **2017**,		1
118	InP nanowire p-type doping via Zinc indiffusion. *Journal of Crystal Growth*, **2016**, 451, 18-26	1.6	3
117	Radial Nanowire Light-Emitting Diodes in the (AlxGa1-x)yIn1-yP Material System. *Nano Letters*, **2016**, 16, 656-62	11.5	31
116	Comparing Hall Effect and Field Effect Measurements on the Same Single Nanowire. *Nano Letters*, **2016**, 16, 205-11	11.5	31
115	Bragg coherent x-ray diffractive imaging of a single indium phosphide nanowire. *Journal of Optics (United Kingdom)*, **2016**, 18, 064007	1.7	25
114	Translocation of 40 nm diameter nanowires through the intestinal epithelium of Daphnia magna. *Nanotoxicology*, **2016**, 10, 1160-7	5.3	22
113	Doping evaluation of InP nanowires for tandem junction solar cells. *Nanotechnology*, **2016**, 27, 065706	3.4	13
112	Strategies to obtain pattern fidelity in nanowire growth from large-area surfaces patterned using nanoimprint lithography. *Nano Research*, **2016**, 9, 2852-2861	10	45
111	Confinement effects on Brillouin scattering in semiconductor nanowire photonic crystal. *Physical Review B*, **2016**, 94,	3.3	6
110	Study of carrier concentration in single InP nanowires by luminescence and Hall measurements. *Nanotechnology*, **2015**, 26, 045705	3.4	34
109	Structural Properties of wurtzite InP-InGaAs nanowire core-shell heterostructures. *Nano Letters*, **2015**, 15, 2462-7	11.5	27
108	In situ characterization of nanowire dimensions and growth dynamics by optical reflectance. *Nano Letters*, **2015**, 15, 3597-602	11.5	44

107	Carrier Recombination Dynamics in Sulfur-Doped InP Nanowires. *Nano Letters*, **2015**, 15, 7238-44	11.5	24
106	Photon upconversion in degenerately sulfur doped InP nanowires. *Nanoscale*, **2015**, 7, 20503-9	7.7	1
105	III-V nanowire synthesis by use of electrodeposited gold particles. *Nano Letters*, **2015**, 15, 134-8	11.5	21
104	Growth parameter design for homogeneous material composition in ternary Ga(x)In(1-x)P nanowires. *Nanotechnology*, **2015**, 26, 435601	3.4	17
103	Doping GaP Core-Shell Nanowire pn-Junctions: A Study by Off-Axis Electron Holography. *Small*, **2015**, 11, 2687-95	11	20
102	A comparative study of absorption in vertically and laterally oriented InP core-shell nanowire photovoltaic devices. *Nano Letters*, **2015**, 15, 1809-14	11.5	49
101	Synthesis of doped InP core-shell nanowires evaluated using hall effect measurements. *Nano Letters*, **2014**, 14, 749-53	11.5	28
100	Absorption of light in InP nanowire arrays. *Nano Research*, **2014**, 7, 816-823	10	68
99	Growth and characterization of wurtzite GaP nanowires with control over axial and radial growth by use of HCl in-situ etching. *Journal of Crystal Growth*, **2014**, 386, 47-51	1.6	30
98	Study of photocurrent generation in InP nanowire-based p+-i-n+ photodetectors. *Nano Research*, **2014**, 7, 544-552	10	35
97	Au-seeded growth of vertical and in-plane III-V nanowires on graphite substrates. *Nano Letters*, **2014**, 14, 1707-13	11.5	31
96	InN quantum dots on GaN nanowires grown by MOVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 421-424		4
95	Evaluation of Doping in GaP Core-Shell Nanowire pn Junction by Off-Axis Electron Holography. *Microscopy and Microanalysis*, **2014**, 20, 288-289	0.5	2
94	Bulk-like transverse electron mobility in an array of heavily n-doped InP nanowires probed by terahertz spectroscopy. *Physical Review B*, **2014**, 90,	3.3	21
93	FIB plan and side view cross-sectional TEM sample preparation of nanostructures. *Microscopy and Microanalysis*, **2014**, 20, 133-40	0.5	20
92	In situ etching for control over axial and radial III-V nanowire growth rates using HBr. *Nanotechnology*, **2014**, 25, 505601	3.4	8
91	Semiconductor nanostructures enabled by aerosol technology. *Frontiers of Physics*, **2014**, 9, 398-418	3.7	18
90	Large-energy-shift photon upconversion in degenerately doped InP nanowires by direct excitation into the electron gas. *Nano Research*, **2013**, 6, 752-757	10	5

89	Fluorescent nanowire heterostructures as a versatile tool for biology applications. *Nano Letters*, **2013**, 13, 4728-32	11.5	38
88	Photoluminescence study of Zn-doped wurtzite InP core-shell nanowiresa). *Applied Physics Letters*, **2013**, 102, 032105	3.4	1
87	Semiconductor-oxide heterostructured nanowires using postgrowth oxidation. *Nano Letters*, **2013**, 13, 5961-6	11.5	7
86	InP nanowire array solar cells achieving 13.8% efficiency by exceeding the ray optics limit. *Science*, **2013**, 339, 1057-60	33.3	962
85	Structural investigation of GaInP nanowires using X-ray diffraction. *Thin Solid Films*, **2013**, 543, 100-105	2.2	15
84	Optical far-field method with subwavelength accuracy for the determination of nanostructure dimensions in large-area samples. *Nano Letters*, **2013**, 13, 2662-7	11.5	13
83	Photoluminescence study of as-grown vertically standing wurtzite InP nanowire ensembles. *Nanotechnology*, **2013**, 24, 115706	3.4	12
82	Current-voltage characterization of individual as-grown nanowires using a scanning tunneling microscope. *Nano Letters*, **2013**, 13, 5182-9	11.5	16
81	Solid-liquid-vapor metal-catalyzed etching of lateral and vertical nanopores. *Nanotechnology*, **2013**, 24, 415303	3.4	4
80	Reflection measurements to reveal the absorption in nanowire arrays. *Optics Letters*, **2013**, 38, 1449-51	3	11
79	Transparently wrap-gated semiconductor nanowire arrays for studies of gate-controlled photoluminescence **2013**,		1
78	Optical characterization of InAs quantum wells and dots grown radially on wurtzite InP nanowires. *Nanotechnology*, **2013**, 24, 225203	3.4	11
77	A luminescence study of doping effects in InP-based radial nanowire structures. *Journal of Physics: Conference Series*, **2013**, 471, 012040	0.3	1
76	High-Performance InAs Nanowire MOSFETs. *IEEE Electron Device Letters*, **2012**, 33, 791-793	4.4	53
75	Electron trapping in InP nanowire FETs with stacking faults. *Nano Letters*, **2012**, 12, 151-5	11.5	90
74	Tunnel field-effect transistors based on InP-GaAs heterostructure nanowires. *ACS Nano*, **2012**, 6, 3109-13	16.7	76
73	Surface chemistry, structure, and electronic properties from microns to the atomic scale of axially doped semiconductor nanowires. *ACS Nano*, **2012**, 6, 9679-89	16.7	35
72	Electrical and optical properties of InP nanowire ensemble p+-i-n+ photodetectors. *Nanotechnology* , **2012**, 23, 135201	3.4	30

71	Particle-assisted Ga(x)In(1-x)P nanowire growth for designed bandgap structures. *Nanotechnology*, **2012**, 23, 245601	3.4	41
70	Single GaInP nanowire p-i-n junctions near the direct to indirect bandgap crossover point. *Applied Physics Letters*, **2012**, 100, 251103	3.4	12
69	Unit cell parameters of wurtzite InP nanowires determined by x-ray diffraction. *Nanotechnology*, **2011**, 22, 425704	3.4	45
68	A new route toward semiconductor nanospintronics: highly Mn-doped GaAs nanowires realized by ion-implantation under dynamic annealing conditions. *Nano Letters*, **2011**, 11, 3935-40	11.5	43
67	Axial InP nanowire tandem junction grown on a silicon substrate. *Nano Letters*, **2011**, 11, 2028-31	11.5	104
66	Growth of doped InAsyP1 nanowires with InP shells. *Journal of Crystal Growth*, **2011**, 331, 8-14	1.6	27
65	Electron image series reconstruction of twin interfaces in InP superlattice nanowires. *Microscopy and Microanalysis*, **2011**, 17, 752-8	0.5	4
64	Nanowires With Promise for Photovoltaics. *IEEE Journal of Selected Topics in Quantum Electronics*, **2011**, 17, 1050-1061	3.8	108
63	Dynamics of extremely anisotropic etching of InP nanowires by HCl. *Chemical Physics Letters*, **2011**, 502, 222-224	2.5	11
62	Valence band splitting in wurtzite InP nanowires observed by photoluminescence and photoluminescence excitation spectroscopy. *Nano Research*, **2011**, 4, 159-163	10	38
61	Gate-induced fermi level tuning in InP nanowires at efficiency close to the thermal limit. *Nano Letters*, **2011**, 11, 1127-30	11.5	16
60	Probing the wurtzite conduction band structure using state filling in highly doped InP nanowires. *Nano Letters*, **2011**, 11, 2286-90	11.5	62
59	Temperature and frequency characterization of InAs nanowire and HfO2 interface using capacitanceoltage method. *Microelectronic Engineering*, **2011**, 88, 444-447	2.5	2
58	Fabrication and characterization of AlP-GaP core-shell nanowires. *Journal of Crystal Growth*, **2011**, 324, 290-295	1.6	6
57	Doping profile of InP nanowires directly imaged by photoemission electron microscopy. *Applied Physics Letters*, **2011**, 99, 233113	3.4	15
56	InAs quantum dots and quantum wells grown on stacking-fault controlled InP nanowires with wurtzite crystal structure. *Applied Physics Letters*, **2011**, 99, 131915	3.4	29
55	Degenerate p-doping of InP nanowires for large area tunnel diodes. *Applied Physics Letters*, **2011**, 99, 253105	3.4	27
54	Doping of semiconductor nanowires. *Journal of Materials Research*, **2011**, 26, 2142-2156	2.5	126

53	Time-resolved photoluminescence investigations on HfO2-capped InP nanowires. *Nanotechnology*, **2010**, 21, 105711	3.4	13
52	Integration, gap formation, and sharpening of III-V heterostructure nanowires by selective etching. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2010**, 28, 21-26	1.3	12
51	Bias-controlled friction of InAs nanowires on a silicon nitride layer studied by atomic force microscopy. *Physical Review B*, **2010**, 82,	3.3	12
50	Doping Incorporation in InAs nanowires characterized by capacitance measurements. *Journal of Applied Physics*, **2010**, 108, 054306	2.5	39
49	Changes in contact angle of seed particle correlated with increased zincblende formation in doped InP nanowires. *Nano Letters*, **2010**, 10, 4807-12	11.5	77
48	Probing strain in bent semiconductor nanowires with Raman spectroscopy. *Nano Letters*, **2010**, 10, 1280-6	11.5	79
47	High-performance single nanowire tunnel diodes. *Nano Letters*, **2010**, 10, 974-9	11.5	73
46	The electrical and structural properties of n-type InAs nanowires grown from metal-organic precursors. *Nanotechnology*, **2010**, 21, 205703	3.4	83
45	In situ etching for total control over axial and radial nanowire growth. *Nano Research*, **2010**, 3, 264-270	10	119
44	Diameter-dependent conductance of InAs nanowires. *Journal of Applied Physics*, **2009**, 106, 124303	2.5	72
43	Determination of the wurtzite content and orientation distribution of nanowire ensembles. *Materials Research Society Symposia Proceedings*, **2009**, 1206, 113901		
42	Preferential Interface Nucleation: An Expansion of the VLS Growth Mechanism for Nanowires. *Advanced Materials*, **2009**, 21, 153-165	24	272
41	Orientation-dependent optical-polarization properties of single quantum dots in nanowires. *Small*, **2009**, 5, 2134-8	11	30
40	Zinc incorporation via the vapor-liquid-solid mechanism into InP nanowires. *Journal of the American Chemical Society*, **2009**, 131, 4578-9	16.4	38
39	Twinning superlattices in indium phosphide nanowires. *Nature*, **2008**, 456, 369-72	50.4	566
38	Precursor evaluation for in situ InP nanowire doping. *Nanotechnology*, **2008**, 19, 445602	3.4	88
37	Local and anisotropic excitation of surface plasmon polaritons by semiconductor nanowires. *Optics Express*, **2008**, 16, 5013-21	3.3	7
36	Epitaxial Growth of III-V Nanowires on Group IV Substrates. *Materials Research Society Symposia Proceedings*, **2008**, 1068, 1		7

35	Epitaxial Growth of Aligned Semiconductor Nanowire Metamaterials for Photonic Applications. *Advanced Functional Materials*, **2008**, 18, 1039-1046	15.6	52
34	Tunable double quantum dots in InAs nanowires. *Physica E: Low-Dimensional Systems and Nanostructures*, **2008**, 40, 1202-1204	3	8
33	Optical Anisotropy of Semiconductor Nanowires **2008**, 127-145		5
32	Three-dimensional morphology of GaP-GaAs nanowires revealed by transmission electron microscopy tomography. *Nano Letters*, **2007**, 7, 3051-5	11.5	79
31	Synergetic nanowire growth. *Nature Nanotechnology*, **2007**, 2, 541-4	28.7	203
30	Remote p-doping of InAs nanowires. *Nano Letters*, **2007**, 7, 1144-8	11.5	70
29	Single quantum dot nanowire LEDs. *Nano Letters*, **2007**, 7, 367-71	11.5	310
28	Epitaxial Growth of III-V Nanowires on Group IV Substrates. *MRS Bulletin*, **2007**, 32, 117-122	3.2	87
27	Tunable few-electron quantum dots in InAs nanowires. *Nanotechnology*, **2007**, 18, 044014	3.4	29
26	Modification of the photoluminescence anisotropy of semiconductor nanowires by coupling to surface plasmon polaritons. *Optics Letters*, **2007**, 32, 2097-9	3	7
25	Interface study on heterostructured GaP-GaAs nanowires. *Nanotechnology*, **2006**, 17, 4010-3	3.4	56
24	Epitaxial III-V Nanowires on Silicon for Vertical Devices. *ECS Transactions*, **2006**, 3, 415-423	1	1
23	Growth kinetics of heterostructured GaP-GaAs nanowires. *Journal of the American Chemical Society*, **2006**, 128, 1353-9	16.4	171
22	Giant optical birefringence in ensembles of semiconductor nanowires. *Applied Physics Letters*, **2006**, 89, 233117	3.4	60
21	Fabrication of Semiconductor Nanowires for Electronic Transport Measurements. *Chimia*, **2006**, 60, 729-734	1.3	20
20	Optically bright quantum dots in single Nanowires. *Nano Letters*, **2005**, 5, 1439-43	11.5	241
19	Enhancement of the electroabsorption in multiple quantum well structures containing a nipi delta-doping superlattice. *Applied Physics Letters*, **2005**, 86, 023501	3.4	1
18	Defect-free InP nanowires grown in [001] direction on InP (001). *Applied Physics Letters*, **2004**, 85, 2077-2079	3.4	159

17	Direct imaging of the atomic structure inside a nanowire by scanning tunnelling microscopy. *Nature Materials*, **2004**, 3, 519-23	27	75
16	Size- and shape-controlled GaAs nano-whiskers grown by MOVPE: a growth study. *Journal of Crystal Growth*, **2004**, 260, 18-22	1.6	104
15	Growth of one-dimensional nanostructures in MOVPE. *Journal of Crystal Growth*, **2004**, 272, 211-220	1.6	255
14	Semiconductor nanowires for 0D and 1D physics and applications. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 25, 313-318	3	143
13	Nanowire Arrays Defined by Nanoimprint Lithography. *Nano Letters*, **2004**, 4, 699-702	11.5	346
12	Arrays of Ge islands on Si(001) grown by means of electron-beam pre-patterning. *Nanotechnology*, **2003**, 14, 264-267	3.4	48
11	Site control of InAs quantum dots on a patterned InP surface: As/P exchange reactions. *Journal of Crystal Growth*, **2003**, 248, 310-316	1.6	
10	InAs quantum dots grown on InAlGaAs lattice matched to InP. *Journal of Crystal Growth*, **2003**, 252, 481-485	1.6	18
9	Fabrication of individually seeded nanowire arrays by vapour□liquid□solid growth. *Nanotechnology*, **2003**, 14, 1255-1258	3.4	177
8	Transport through an isolated artificial molecule formed from stacked self-assembled quantum dots. *Applied Physics Letters*, **2003**, 82, 2655-2657	3.4	21
7	Designed emitter states in resonant tunneling through quantum dots. *Applied Physics Letters*, **2002**, 80, 2681-2683	3.4	25
6	Electron beam pre-patterning for site-control of self-assembled InAs quantum dots on Inp surfaces. *Journal of Electronic Materials*, **2001**, 30, 482-486	1.9	6
5	High peak-to-valley ratios observed in InAs/InP resonant tunneling quantum dot stacks. *Applied Physics Letters*, **2001**, 78, 3232-3234	3.4	36
4	Electron beam prepatterning for site control of self-assembled quantum dots. *Applied Physics Letters*, **2001**, 78, 1367-1369	3.4	18
3	MOVPE overgrowth of metallic features for realisation of 3D metal□semiconductor quantum devices. *Journal of Crystal Growth*, **2000**, 221, 704-712	1.6	13
2	Optical investigation of InAs/InP quantum dots at different temperatures and under electric field. *Thin Solid Films*, **2000**, 364, 161-164	2.2	15
1	Development and characterization of photovoltaic tandem-junction nanowires using electron-beam-induced current measurements. *Nano Research*,	10	1